Digital transistors (built-in resistor) DTC363TK / DTC363TS

Features

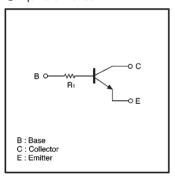
In addition to the features of regular digital transistors.

- Low VcE(sat) makes these transistors optimal for muting circuits.
 VcE(sat) = 40mV (Typ.)
 (Ic/IB = 50mA/2.5mA)
- They can be used at high current (Ic = 600mA).

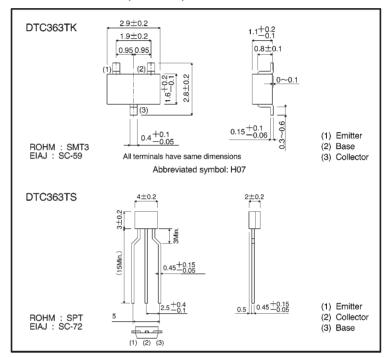
Structure

NPN digital transistor (Built-in resistor type)

Equivalent circuit



External dimensions (Units: mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter	Cumbal	Limits(D	Unit		
	Symbol	К	S	Offic	
Collector-base voltage	Vсво	30		V	
Collector-emitter voltage	VCEO	15		V	
Emitter-base voltage	VEBO	5		V	
Collector current	Ic	600		mA	
Collector power dissipation	Pc	200	300	mW	
Junction temperature	Tj	150		°C	
Storage temperature	Tstg	−55~+150		°C	

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Collector-base breakdown voltage	ВУсво	30	_	_	٧	Ic=50 μ A	
Collector-emitter breakdown voltage	BVCEO	15	_	_	٧	lc=1mA	
Emitter-base breakdown voltage	ВVево	5	_	_	٧	IE=50 μ A	
Collector cutoff current	Ісво	_	_	0.5	μΑ	V _{CB} =20V	
Emitter cutoff current	IЕВО	_	_	0.5	μΑ	V _{EB} =4V	
Collector-emitter saturation voltage	V _{CE} (sat)	_	40	80	mV	Ic/Iв=50mA/2.5mA	
DC current transfer ratio	hre	100	250	600	_	VcE=5V, Ic=50mA	
Input resistance	Rı	4.76	6.8	8.84	kΩ	_	
Transition frequency	fτ	_	200	_	MHz	VcE=10V, IE=-50mA, f=100MHz *	
Output "ON" resistance	Ron	_	1.25	_	Ω	$V_1=7V$, $R_L=1k\Omega$, $f=1kHz$	

^{*} Transition frequency of the device

Packaging specifications

	Package	SMT3	SPT
	Packaging type	Taping	Taping
	Code T146		TP
Part No.	Basic ordering unit (pieces)	3000	5000
DTC363TK		0	_
DTC363TS		_	0

■Ron measurement circuit

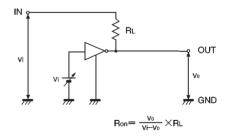


Fig.1 Input "on" resistance (Ron) measurement circuit

Electrical characteristic curves

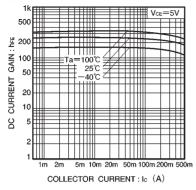


Fig.2 DC current gain vs. collector current

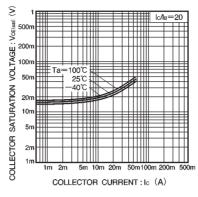


Fig.3 Collector-emitter saturation voltage vs. collector current

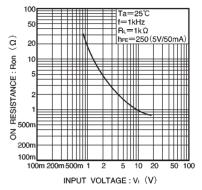


Fig.4 "ON" resistance vs. input voltage